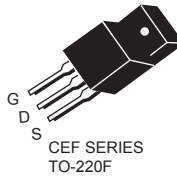
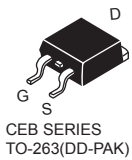


## N-Channel Enhancement Mode Field Effect Transistor

### FEATURES

Type	V <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub>	@V <sub>GS</sub>
CEP630N	200V	0.36Ω	9A	10V
CEB630N	200V	0.36Ω	9A	10V
CEF630N	200V	0.36Ω	9A <sup>d</sup>	10V

- Super high dense cell design for extremely low R<sub>DS(ON)</sub>.
- High power and current handling capability.
- Lead free product is acquired.



### ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263	TO-220F	
Drain-Source Voltage	V <sub>DS</sub>	200		V
Gate-Source Voltage	V <sub>GS</sub>	±20		V
Drain Current-Continuous	I <sub>D</sub>	9	9 <sup>d</sup>	A
Drain Current-Pulsed <sup>a</sup>	I <sub>DM</sub> <sup>e</sup>	36	36 <sup>d</sup>	A
Maximum Power Dissipation @ T <sub>C</sub> = 25°C - Derate above 25°C	P <sub>D</sub>	78	33	W
		0.63	0.27	W/°C
Operating and Store Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150		°C

### Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	1.6	3.7	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	62.5	65	°C/W



# CEP630N/CEB630N CEF630N

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	200			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 160V, V_{GS} = 0V$			25	$\mu A$
Gate Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS} = 20V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS} = -20V, V_{DS} = 0V$			-100	nA
<b>On Characteristics<sup>b</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5A$		0.30	0.36	$\Omega$
<b>Dynamic Characteristics<sup>c</sup></b>						
Forward Transconductance	$g_{FS}$	$V_{DS} = 10V, I_D = 5A$		4		S
Input Capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{ MHz}$		930		pF
Output Capacitance	$C_{oss}$			130		pF
Reverse Transfer Capacitance	$C_{rss}$			25		pF
<b>Switching Characteristics<sup>c</sup></b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100V, I_D = 5A, V_{GS} = 10V, R_{GEN} = 50\Omega$		24	48	ns
Turn-On Rise Time	$t_r$			15	30	ns
Turn-Off Delay Time	$t_{d(off)}$			116	232	ns
Turn-Off Fall Time	$t_f$			25	50	ns
Total Gate Charge	$Q_g$	$V_{DS} = 160V, I_D = 5.9A, V_{GS} = 10V$		19	24.7	nC
Gate-Source Charge	$Q_{gs}$			3		nC
Gate-Drain Charge	$Q_{gd}$			5		nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Current	$I_S^f$				9	A
Drain-Source Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 9A^g$			1.5	V
<b>Notes :</b> □ a.Repetitive Rating : Pulse width limited by maximum junction temperature . b.Pulse Test : Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$ . □ c.Guaranteed by design, not subject to production testing. □ d.Limited only by maximum temperature allowed . e.Pulse width limited by safe operating area . f.Full package $I_{S(max)} = 5.9A$ . g.Full package $V_{SD}$ test condition $I_S = 5.9A$ .						



# CEP630N/CEB630N CEF630N

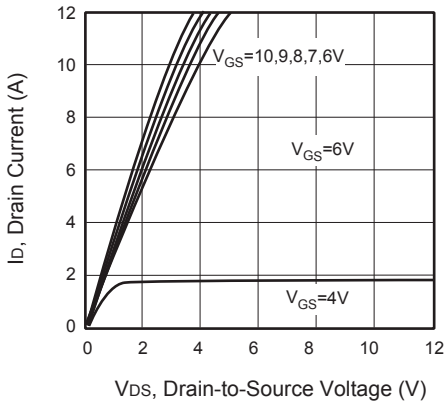


Figure 1. Output Characteristics

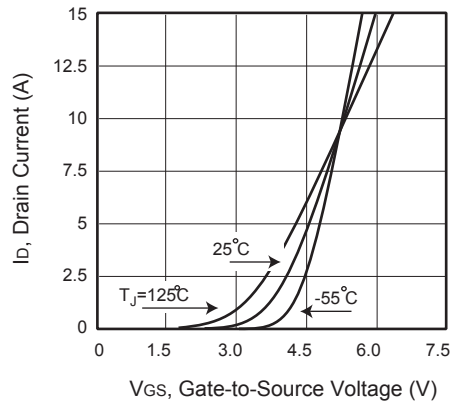


Figure 2. Transfer Characteristics

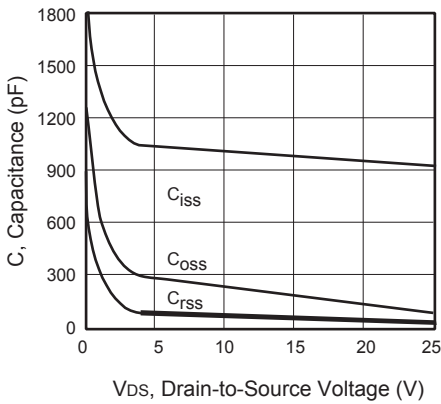


Figure 3. Capacitance

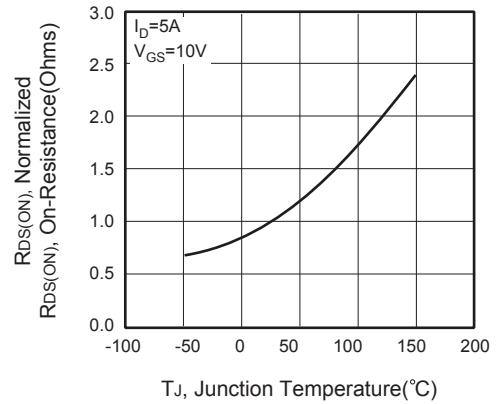


Figure 4. On-Resistance Variation with Temperature

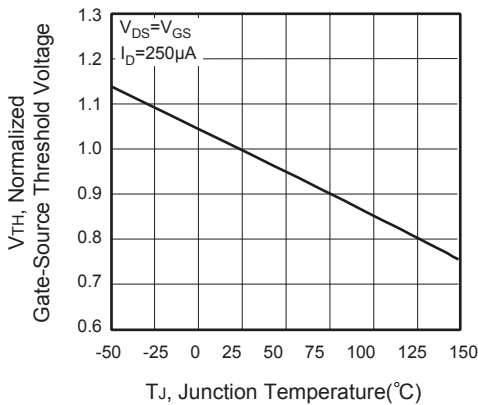


Figure 5. Gate Threshold Variation with Temperature

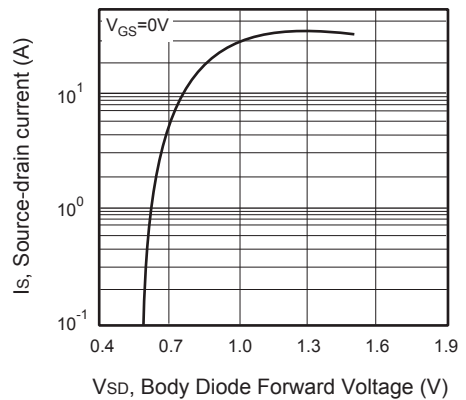


Figure 6. Body Diode Forward Voltage Variation with Source Current

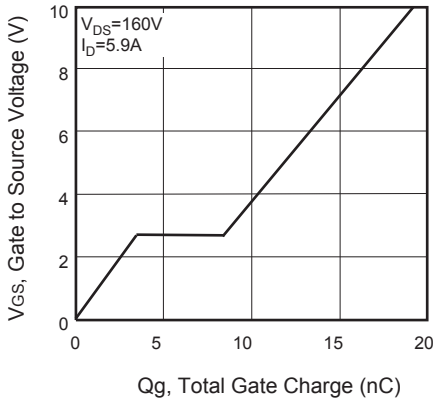


Figure 7. Gate Charge

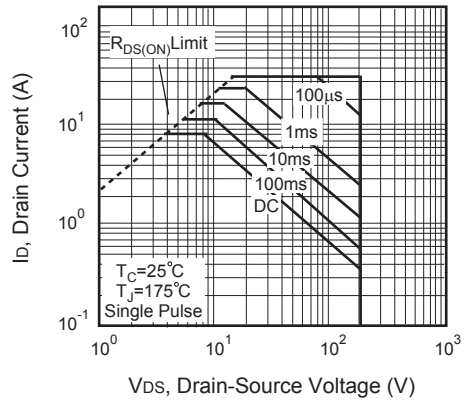


Figure 8. Maximum Safe Operating Area

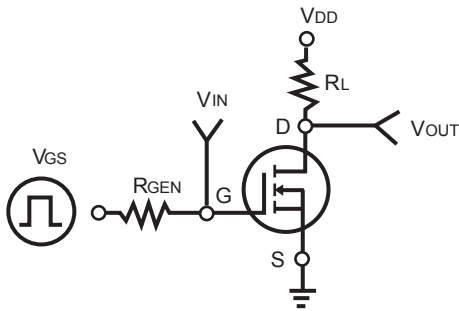


Figure 9. Switching Test Circuit

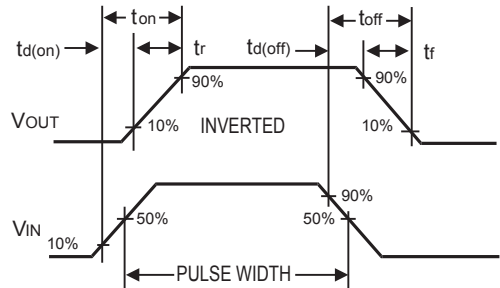


Figure 10. Switching Waveforms

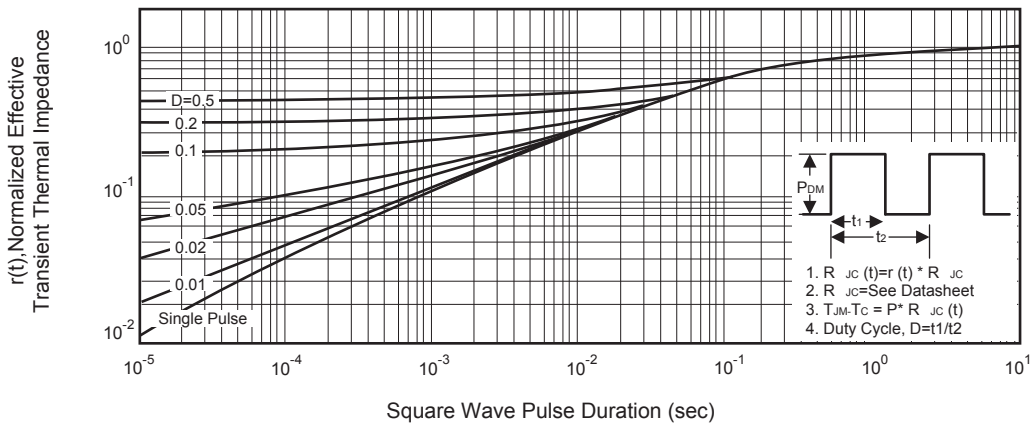


Figure 11. Normalized Thermal Transient Impedance Curve